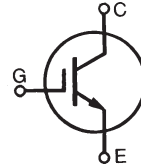


HiPerFAST™ IGBT

IXGP 30N60B2

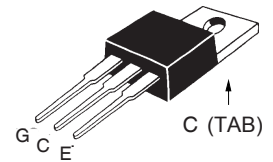
Optimized for 10-25 KHz hard switching and up to 150 KHz resonant switching

$$\begin{aligned}
 V_{CES} &= 600 \text{ V} \\
 I_{C25} &= 70 \text{ A} \\
 V_{CE(sat)} &< 1.8 \text{ V} \\
 t_{fi typ} &= 82 \text{ ns}
 \end{aligned}$$



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (limited by leads)	70	A
I_{C110}	$T_C = 110^\circ\text{C}$	30	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	150	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 10 \Omega$ Clamped inductive load @ $\leq 600 \text{ V}$	$I_{CM} = 60$	A
P_C	$T_C = 25^\circ\text{C}$	190	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10Nm/lb.in.	
Weight		4	g

TO-220 (IXSP)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

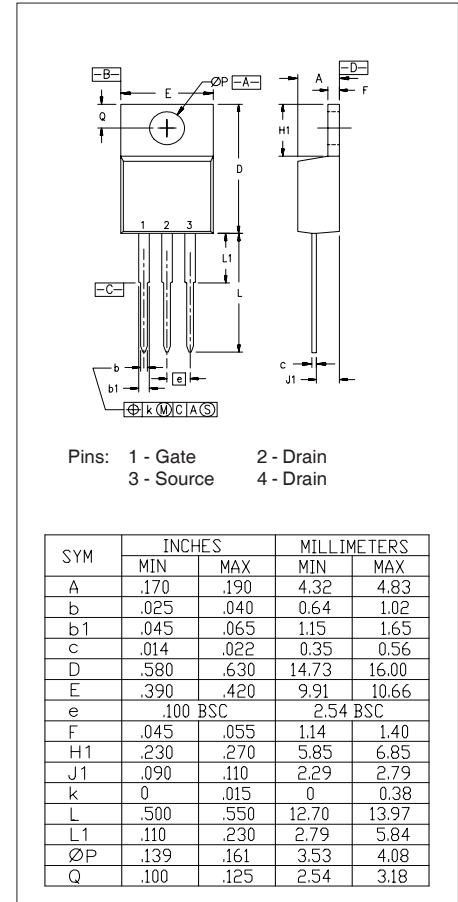
- Medium frequency IGBT
- Square RBSOA
- High current handling capability
- MOS Gate turn-on
- drive simplicity

Applications

- PFC circuits
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{GE(th)}$	$I_C = 250 \mu\text{A}$, $V_{CE} = V_{GE}$	2.5		5.0 V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$			50 μA 1 mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = 24 \text{ A}$, $V_{GE} = 15 \text{ V}$			1.8 V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
g_{fs}	$I_C = 24\text{ A}; V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$	18	26	S	
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		1500	pF	
C_{oes}			115	pF	
C_{res}			40	pF	
Q_g	$I_C = 24\text{ A}, V_{GE} = 15\text{ V}, V_{CE} = 300\text{ V}$		66	nC	
Q_{ge}			9	nC	
Q_{gc}			22	nC	
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 24\text{ A}, V_{GE} = 15\text{ V}$ $V_{CE} = 400\text{ V}, R_G = 5\ \Omega$		13	ns	
t_{ri}			15	ns	
$t_{d(off)}$			110	200	ns
t_{fi}			82	150	ns
E_{off}			0.32	0.6	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 24\text{ A}, V_{GE} = 15\text{ V}$ $V_{CE} = 400\text{ V}, R_G = 5\ \Omega$		13	ns	
t_{ri}			17	ns	
E_{on}			0.22	mJ	
$t_{d(off)}$			200	ns	
t_{fi}			150	ns	
E_{off}		0.9	mJ		
R_{thJC}				0.65	KW
R_{thCH}		0.25			KW



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	6,404,065B1	6,162,665	6,534,343	6,583,505
	4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1	6,259,123B1	6,306,728B1	6,683,344

Fig. 1. Output Characteristics @ 25 Deg. C

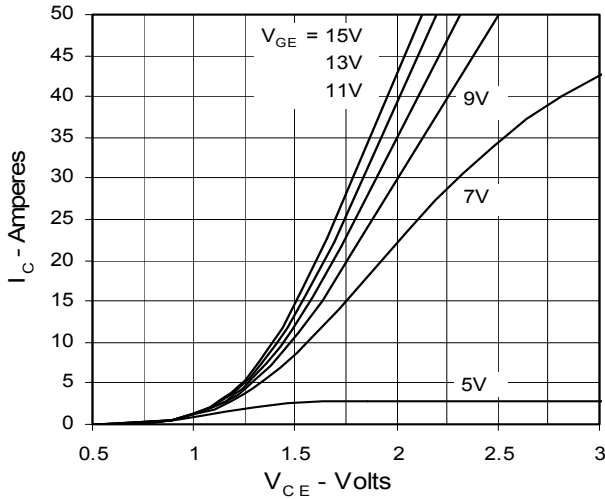


Fig. 2. Extended Output Characteristics @ 25 deg. C

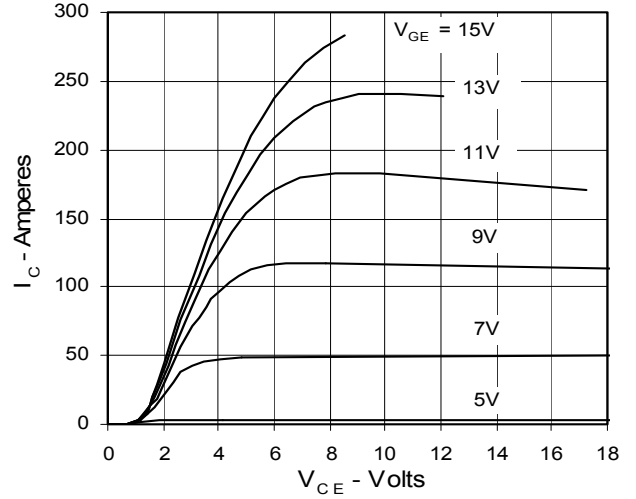


Fig. 3. Output Characteristics @ 125 Deg. C

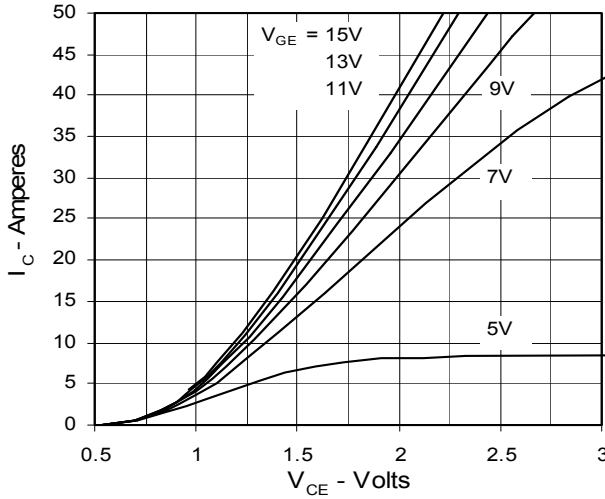


Fig. 4. Dependence of $V_{CE(sat)}$ on Temperature

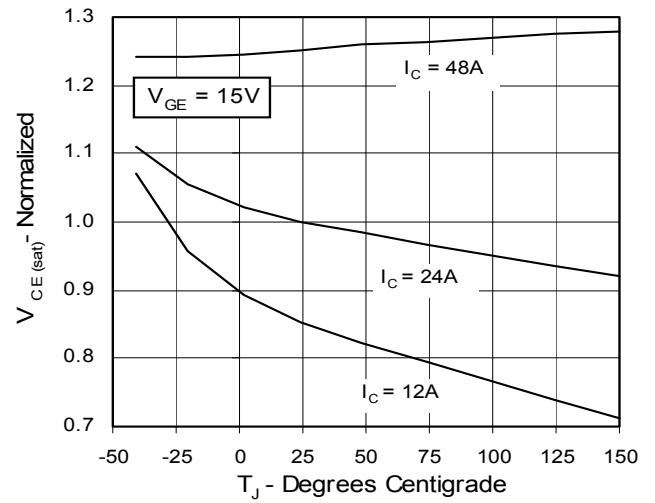


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter voltage

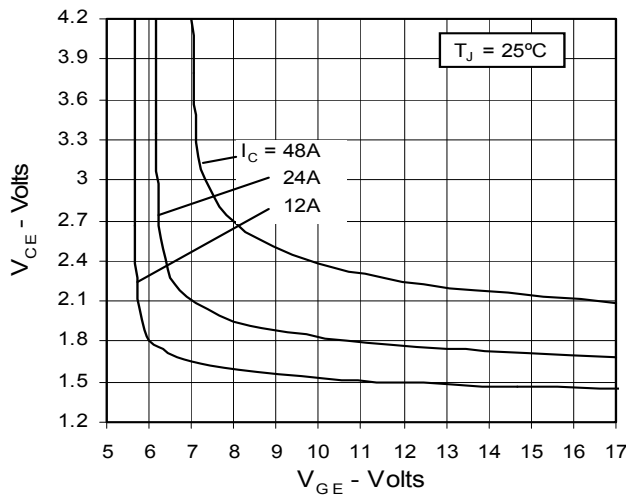


Fig. 6. Input Admittance

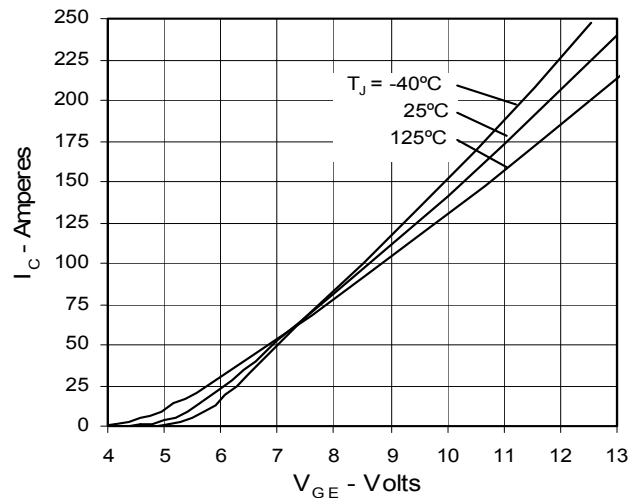
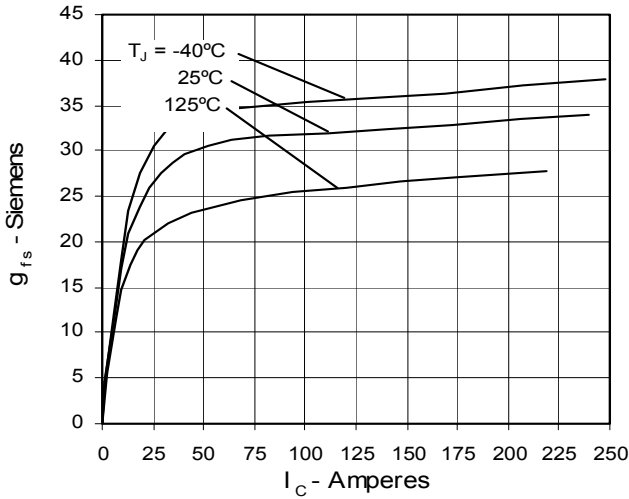
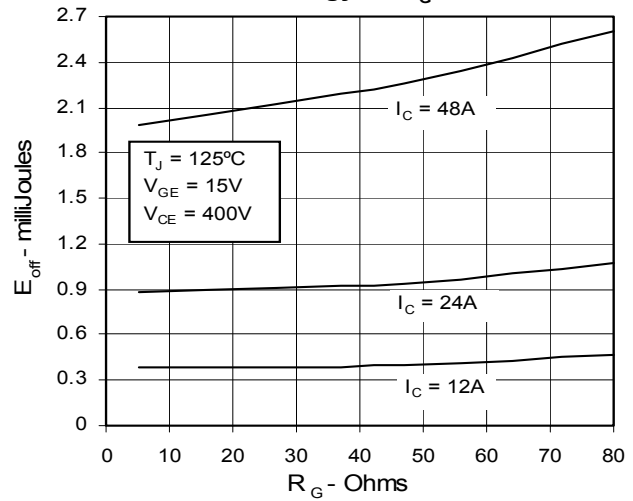
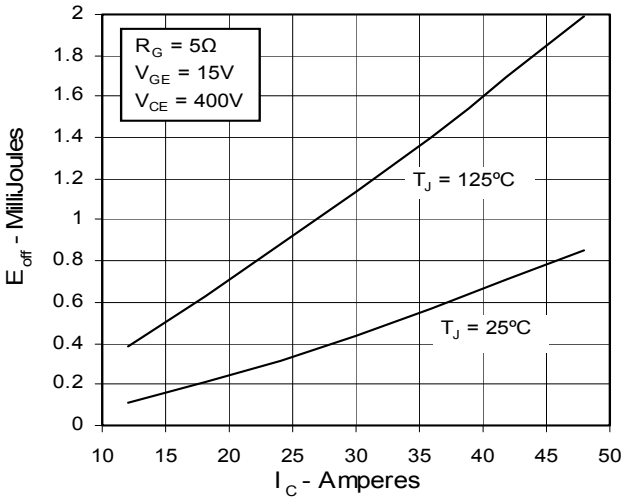
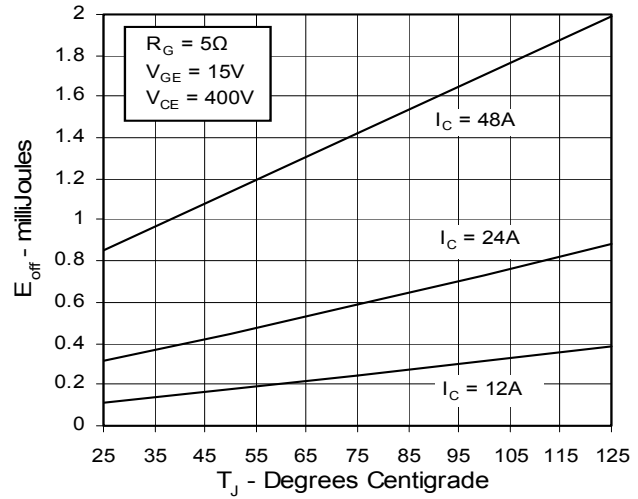
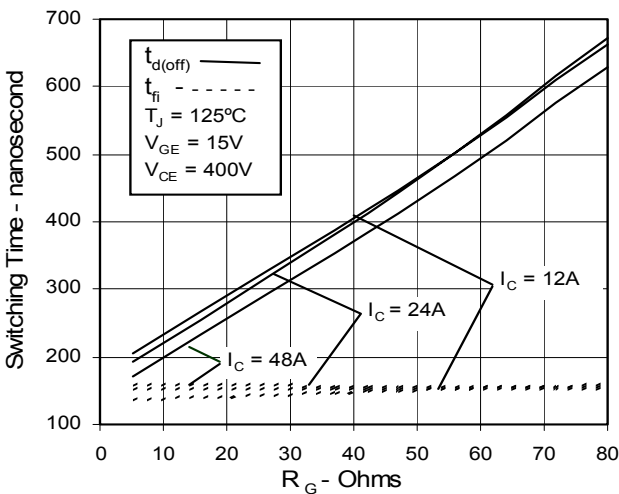
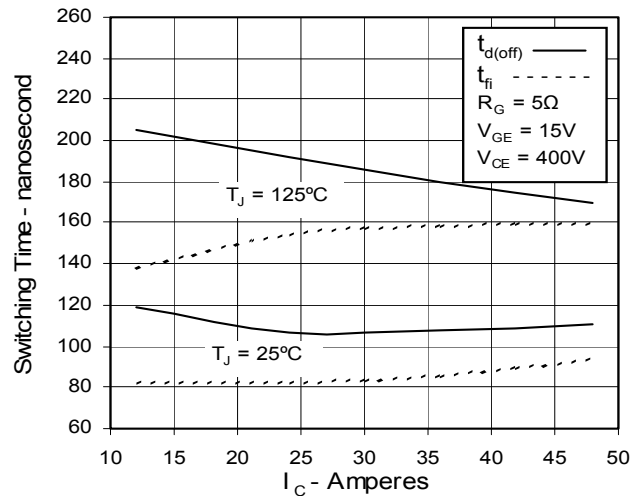


Fig. 7. Transconductance

Fig. 8. Dependence of Turn-Off Energy on R_G

Fig. 9. Dependence of Turn-Off Energy on I_C

Fig. 10. Dependence of Turn-Off Energy on Temperature

Fig. 11. Dependence of Turn-Off Switching Time on R_G

Fig. 12. Dependence of Turn-Off Switching Time on I_C


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4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	6,404,065B1	6,162,665	6,534,343	6,583,505
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Fig. 13. Dependence of Turn-Off Switching Time on Temperature

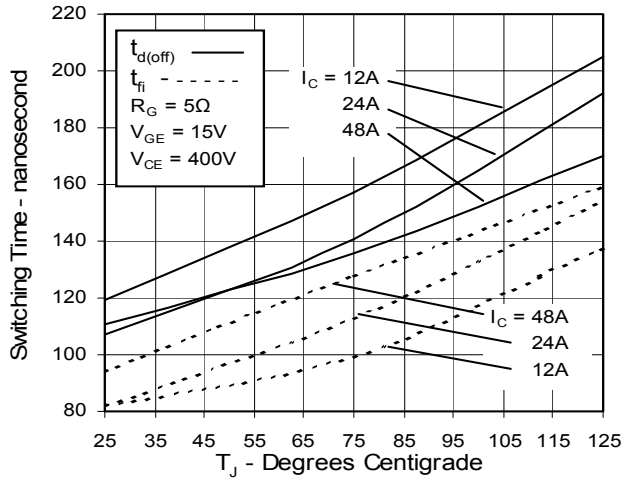


Fig. 14. Gate Charge

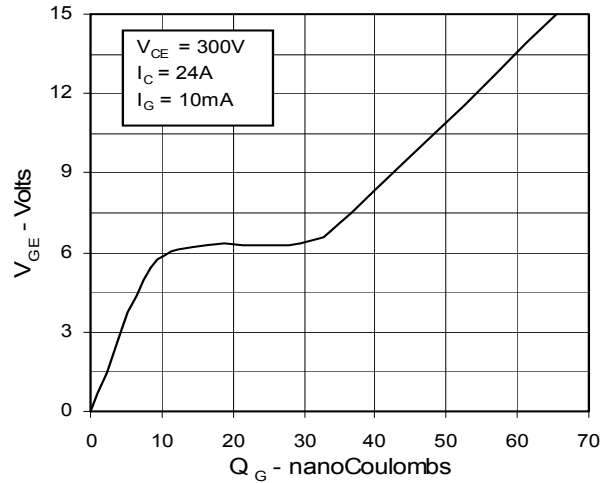


Fig. 15. Capacitance

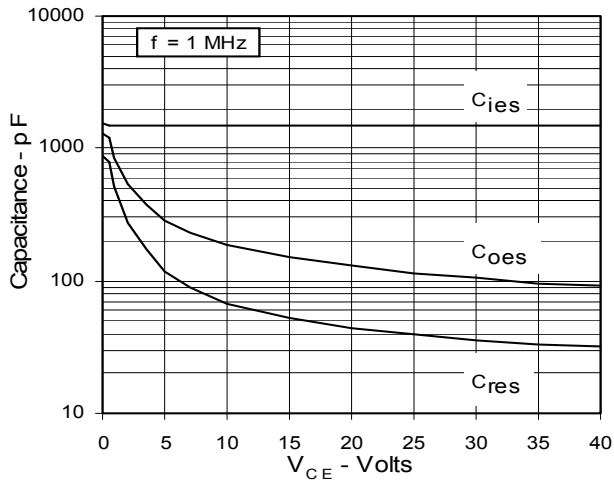


Fig. 16. Maximum Transient Thermal Resistance

